

# Fabrication of BaTiO<sub>3</sub>-PTFE composite film for embedded capacitor employing aerosol deposition

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## Abstract

The potential for using aerosol deposition (AD) as an alternative fabrication method to the conventional polymer composite process for embedded capacitors was examined. In order to achieve a high relative dielectric permittivity, BaTiO<sub>3</sub>-polytetrafluoroethylene (PTFE) composite thick films were attempted by AD at room temperature. For the high dielectric constant, the BaTiO<sub>3</sub>-PTFE composite films grown by AD should satisfied the following two critical conditions: a reduced decrement in ceramic particle size and a relieved distortion of the crystal structure. However, the relative permittivity of the composite films was too low compared with that of the BaTiO<sub>3</sub> films grown by AD. By predicting the dielectric constant in several composite models using the Hashin–Shtrikman bounds theory and 3-dimensional (3-D) electrostatic simulation, we confirmed that the connectivity between ceramic particles is a highly critical factor for achieving a high dielectric constant in composite films. © 2011 Elsevier Ltd and Techna Group S.r.l. All rights reserved.

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## 1. Introduction

With the digital convergence of information technology, telecommunication, consumer electronics, and entertainment, research and development is focusing on the 3-dimensional (3-D) integrations of electronic components by means of embedded planar technologies. Especially, the widely used decoupling capacitors must be changed from surface mount technologies to embedded planar technologies due to the high-frequency operation and the large occupation percentage of decoupling capacitors in today's electronic devices [1]. The fabrication of such embedded planar decoupling capacitors requires low-temperature technologies for the development of ceramic materials as such materials generally need high processing temperatures above 1000 °C. In order to overcome this problem, polymer composites have been investigated, but they suffered due to low ceramic contents of below 60 vol.% in the composites and low dielectric constant [2–4].

Our research group has focused on the aerosol deposition (AD) process as a novel, low-temperature process for developing embedded decoupling capacitors with high capacitance density due to its superior merits of room temperature processing, high deposition rate, and high density. However, the relative permittivity of BaTiO<sub>3</sub> films aerosol-deposited at room temperature was sharply reduced to approximately 100 from the general range of 1000–3000 that is typical for BaTiO<sub>3</sub> powder. This abrupt decrease in their relative permittivity was attributed to the collision impact of particles in the AD process [5,6]. During the AD process, accelerated ceramic particles are ejected through a nozzle and then impacted at a velocity of 200–300 m/s onto a substrate to form nano-sized BaTiO<sub>3</sub> films. These particle collision impacts cause crystal lattice distortion, internal stress, and small crystallite size in BaTiO<sub>3</sub> films grown by AD.

In our previous research on flexible integrated substrates fabricated by AD, we attempted to fabricate the ceramic-polymer composite thick films by AD to overcome the problems of ceramic materials, such as brittleness and fragileness. Al<sub>2</sub>O<sub>3</sub>-polymer composite thick films were successfully fabricated by AD and its good dielectric properties

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were confirmed [7–9]. The decrement of the crystallite size of  $\text{Al}_2\text{O}_3$  ceramics in  $\text{Al}_2\text{O}_3$ -polymer composite films was reduced due to the cushion-effect of the polymer.

In this paper, this polymer elasticity is used to relieve the collision impact of  $\text{BaTiO}_3$  particles in the AD process and hence facilitate the fabrication of  $\text{BaTiO}_3$ -PTFE composite films with high dielectric constant. Additionally, several ceramic-polymer composite models are designed and their permittivity is calculated by 3-D electrostatic simulation to confirm the causes of the polymer composite's low dielectric constant.

## 2. Experimental

The AD process is based on shock loading solidification due to the impact of ultra-fine particles accelerated through a nozzle by carrier gases, as described elsewhere [10,11].  $\text{BaTiO}_3$  and  $\text{BaTiO}_3$ -PTFE composite films were prepared by AD by using commercial  $\text{BaTiO}_3$  powders (BT-04, SAKAI CHEMICAL INDUSTRY CO., Ltd., Japan) with a particle size of  $0.45\ \mu\text{m}$  as starting powders. The particles were aerosolized in an aerosol chamber and transported into a deposition chamber by He gas at a flow rate of 7 L/min. The orifice size of the nozzle was  $10 \times 0.4\ \text{mm}^2$ , the deposition area  $10 \times 10\ \text{mm}^2$ , the distance between the substrates 10 mm, the working pressure 21 Torr, and the deposition time 1 min 30 s. For the fabrication of the  $\text{BaTiO}_3$ -PTFE composite films by AD, PTFE powders (Daikin POLYFLON L-5 PTFE Low polymer, DAIKIN INDUSTRIES, Ltd., Japan) with a particle size of  $0.15\ \mu\text{m}$  and the aforementioned  $\text{BaTiO}_3$  powders were chosen as starting powders. A  $\text{BaTiO}_3$ -PTFE mixed powder with a PTFE powder

content of 0.1 wt.% was prepared, milled with ethanol for 24 h and dried at  $80\ ^\circ\text{C}$  for 48 h. The  $\text{BaTiO}_3$ -PTFE composite films were fabricated at room temperature by AD. The He gas flow rate was 4 L/min, the working pressure 5.5 Torr, and the deposition time 5 min. The other conditions were the same as those of the aerosol-deposited  $\text{BaTiO}_3$  films. The surface morphologies of the films were observed using a field-emission scanning electron microscopy (FE-SEM, S-4700, HITACHI Ltd., Japan). Next, the crystallinity and crystallite size were analyzed by using an X-ray diffractometer (XRD, X'Pert PRO, PAN alytical). Finally, the dielectric properties of the films were measured using an impedance analyzer (HP 4194A, Agilent). Various simulation models were designed and their permittivity calculated using 3-D electrostatic simulation (ANSYS Ver.12.10, ANSYS, Inc.) in order to confirm the causes of low permittivity in the composite films.

## 3. Results and discussion

### 3.1. Microstructures of the $\text{BaTiO}_3$ and $\text{BaTiO}_3$ -PTFE composite films fabricated by AD process

The  $\text{BaTiO}_3$  and  $\text{BaTiO}_3$ -PTFE composite films were successfully fabricated on Cu and glass substrates by AD. The aerosol-deposited  $\text{BaTiO}_3$  films were dense without any pores, as shown in Fig. 1(a) and (c). However, the XRD pattern of the  $\text{BaTiO}_3$  films exhibited a slight peak shift in comparison with that of the as-received  $\text{BaTiO}_3$  powders, as shown in Fig. 2(a) and (b). The calculated crystallite size of these films according to Scherrer equation was 11.2 nm based on the 110 peak. The distortion of the crystal structure and the internal

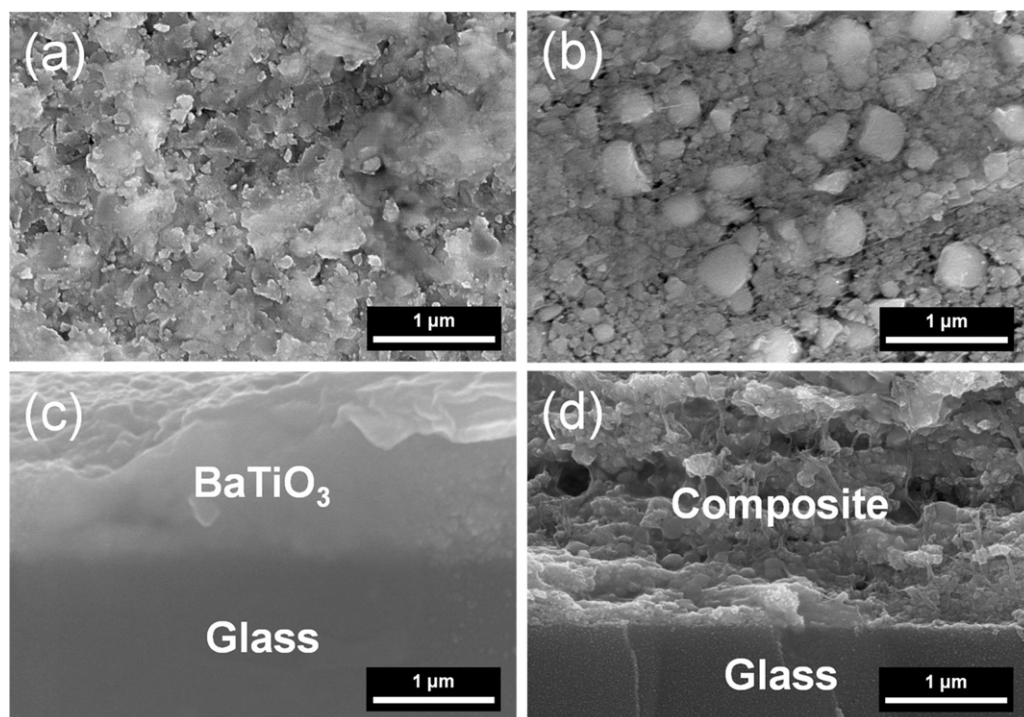


Fig. 1. Surface SEM images of the (a)  $\text{BaTiO}_3$  and (b)  $\text{BaTiO}_3$ -PTFE composite films and cross-sectional SEM images of the (c)  $\text{BaTiO}_3$  and (d)  $\text{BaTiO}_3$ -PTFE composite films on glass substrates.

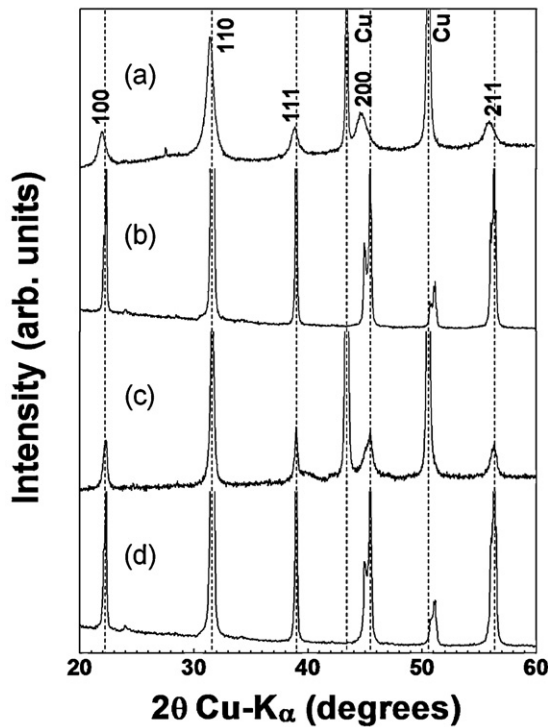


Fig. 2. X-ray diffraction patterns of the (a) BaTiO<sub>3</sub> films on Cu substrates, (b) BaTiO<sub>3</sub> starting powders, (c) BaTiO<sub>3</sub>-PTFE composite films on Cu substrates, and (d) BaTiO<sub>3</sub>-PTFE starting powders.

stress in the BaTiO<sub>3</sub> films would be confirmed from the peak shift and small crystallites size. On the other hand, the BaTiO<sub>3</sub> particles maintained their particles size in the BaTiO<sub>3</sub>-PTFE composite films, as shown in Fig. 1(b) and (d), and no peak shift was observed in their XRD pattern in comparison with that of the BaTiO<sub>3</sub>-PTFE mixing powders, as shown in Fig. 2(c) and (d). The crystallite size of the BaTiO<sub>3</sub> material in the BaTiO<sub>3</sub>-PTFE composite films was calculated as 24.6 nm based on the 110 peak by using Scherrer equation, which was double that of the BaTiO<sub>3</sub> films. The crystal structure of the BaTiO<sub>3</sub> films was confirmed as cubic phase, as shown in Fig. 3(a). However, the tetragonal phase of the BaTiO<sub>3</sub> material was still existed in the BaTiO<sub>3</sub>-PTFE composite films. Consequently, the decrement in the BaTiO<sub>3</sub> particle size was reduced and the distortion of the

crystal structures was relieved in the BaTiO<sub>3</sub>-PTFE composite films owing to the elasticity of the PTFE material. Fig. 4 illustrated the growth of the BaTiO<sub>3</sub> and composite films.

### 3.2. Dielectric properties of the BaTiO<sub>3</sub> films and BaTiO<sub>3</sub>-PTFE composite films

The relative permittivity and loss tangent of the BaTiO<sub>3</sub> films were 64 and 0.073 at 100 kHz, respectively, as shown in Fig. 5(a). These values agreed well with those previously reported [5,6]. The equivalent values for the BaTiO<sub>3</sub>-PTFE composite films were 15 and 0.091, respectively, as shown in Fig. 5(b). However, contrary to the expectations based on the microstructure observations, this relative permittivity was too low compared with that of the BaTiO<sub>3</sub> films, which was attributed to the content of the ceramic material and the films' inner structure.

### 3.3. Calculation of the dielectric constant of the aerosol-deposited BaTiO<sub>3</sub>-PTFE composite model using 3-D electrostatic simulation

We firstly considered the ceramic content in the composite films as the possible cause of the low permittivity of the aerosol-deposited BaTiO<sub>3</sub>-PTFE composite films. To investigate the effects of ceramic content on the dielectric constant of the composite films, the top and bottom limits for the dependence of the relative permittivity of the composite films on the ceramic content were plotted using Hashin–Shtrikman bounds theory, as shown in Fig. 6(a) [12]. The relative permittivity of the composite films at certain ceramic content was placed within the range of the top ( $\epsilon_T$ ) and bottom ( $\epsilon_B$ ) limits. The top and bottom limits of the composite, consisting of two phases with dielectric constants of  $\epsilon_1$  and  $\epsilon_2$ , are expressed by Eqs. (1) and (2), respectively, where  $d$  means dimension and  $V_1$  and  $V_2$  are the volume fractions of the two phases 1 and 2, respectively. Eqs. (3) and (4) show the definition of  $\langle\epsilon_a\rangle$  and  $\langle\epsilon_b\rangle$ , respectively.

$$\epsilon_T = \langle\epsilon_a\rangle - \frac{V_1 V_2 (\epsilon_2 - \epsilon_1)^2}{\langle\epsilon_b\rangle + (d - 1)\epsilon_2} \quad (1)$$

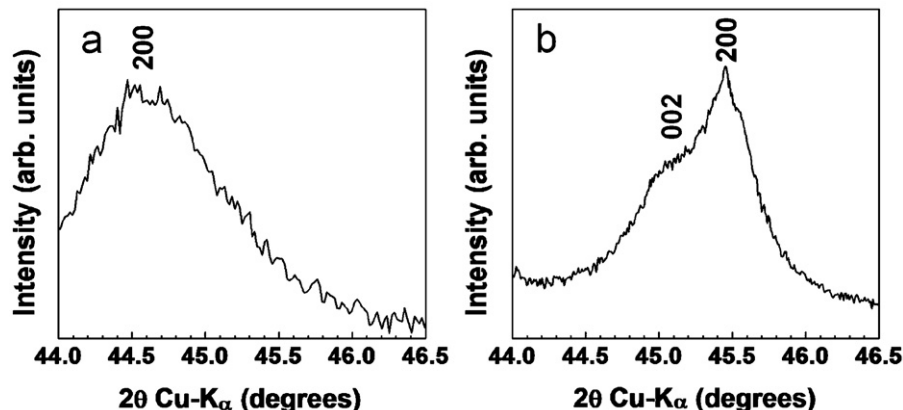


Fig. 3. Enlarged 200 peak of the (a) BaTiO<sub>3</sub> and (b) BaTiO<sub>3</sub>-PTFE composite films fabricated by AD.

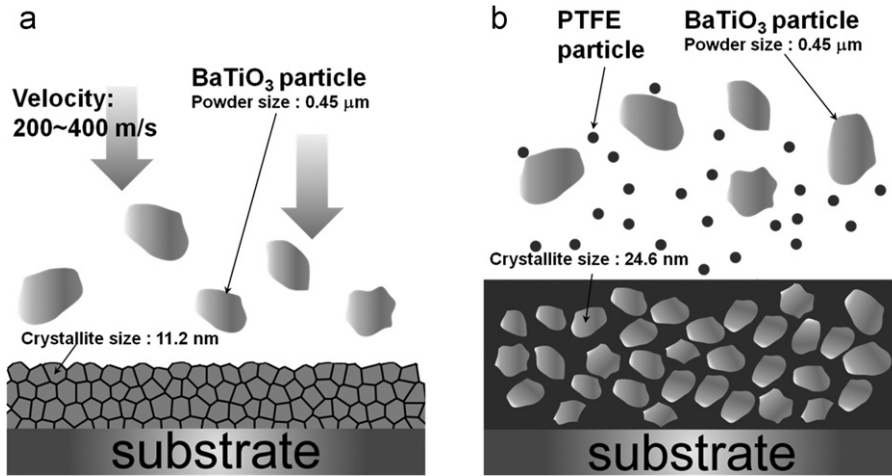


Fig. 4. Schematic diagrams showing the growth of the (a) BaTiO<sub>3</sub> and (b) BaTiO<sub>3</sub>-PTFE composite films fabricated by AD.

$$\varepsilon_B = \langle \varepsilon_a \rangle - \frac{V_1 V_2 (\varepsilon_2 - \varepsilon_1)^2}{\langle \varepsilon_b \rangle + (d-1)\varepsilon_1} \quad (2)$$

$$\langle \varepsilon_a \rangle = \varepsilon_1 V_1 + \varepsilon_2 V_2 \quad (3)$$

$$\langle \varepsilon_b \rangle = \varepsilon_1 V_2 + \varepsilon_2 V_1 \quad (4)$$

This result confirmed the large gap between the top and bottom limits of the dielectric constant. A complete explanation

of the causes of this large gap will facilitate the development of a method capable of fabricating composite films with high permittivity close to the top limit. We ascribed this large gap to the inner structure of the composite films. Therefore, various simulation models based on the planar capacitor model with the BaTiO<sub>3</sub>-PTFE composite layer were designed using 3-D electrostatic simulation by considering the connectivity between ceramic particles. Fig. 6(b) and (c) show the designed contact and non-contact models, respectively. Small cubes and empty parts in the models were assigned as the BaTiO<sub>3</sub> ( $\varepsilon_r = 3000$ ) and PTFE ( $\varepsilon_r = 2.1$ ) materials, respectively. These small cubes in the contact models were perfectly connected with each other but there was no such connectivity in the non-contact models. The size of the planar capacitor model was  $6 \mu\text{m} \times 6 \mu\text{m} \times 3 \mu\text{m}$  and the excitation voltage was 1 V.

The simulations results confirmed the action of two factors in influencing the dielectric constant of the composite films. Firstly, the dielectric constant of the contact models was increased with increasing BaTiO<sub>3</sub> content following the  $\varepsilon_T$  of the Hashin–Shtrikman bounds, as shown in Fig. 6(a). Secondly, the large gap between  $\varepsilon_T$  and  $\varepsilon_B$  resulted from the connectivity between the BaTiO<sub>3</sub> particles. Although the contact model (Fig. 6(b)) with 60.2 vol.% and the non-contact model (Fig. 6(c)) with 60.4 vol.% were assigned with approximately the same BaTiO<sub>3</sub> content, their relative permittivity differed by over 1000. And also, the relative permittivity calculated for the contact and non-contact models with BaTiO<sub>3</sub> contents of 70, 80, and 90 vol.% agreed well with our prediction. Additionally, models with randomly connected BaTiO<sub>3</sub> particles were prepared to confirm the relation between ceramic particle connectivity and their dielectric constant, as shown in Fig. 6(a). Their total BaTiO<sub>3</sub> content was approximately the same at 80 vol.%. Their connected BaTiO<sub>3</sub> volume content was increased from 41.1 to 99.2 vol.%. Fig. 6(d) shows the model with 88.9 vol.% of the BaTiO<sub>3</sub> particles randomly connected and 11.1 vol.% separated. This simulation result demonstrated that the increase in the connectivity between the BaTiO<sub>3</sub> particles directly affected the increase in the dielectric constant of the composite model, as shown in Fig. 6(a). This confirmed

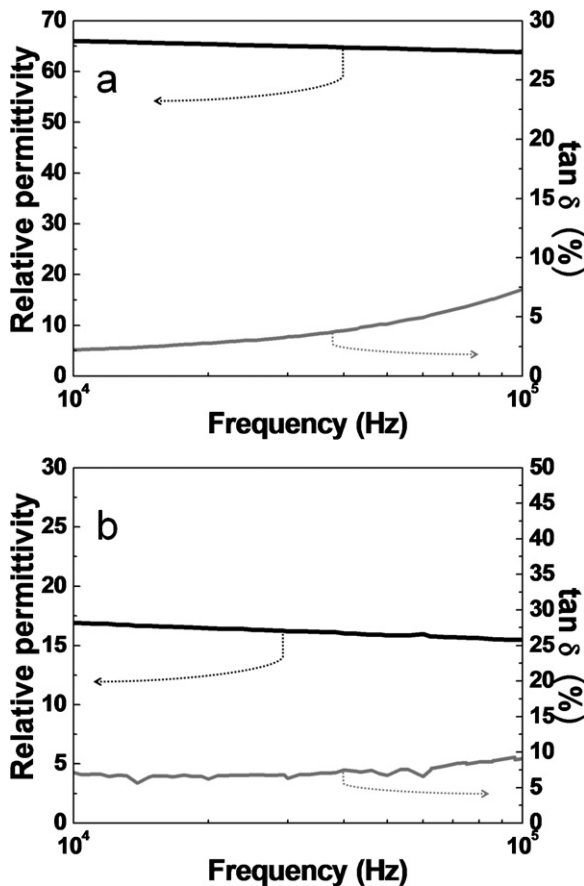


Fig. 5. Frequency dependence of relative permittivity and loss tangent of the (a) BaTiO<sub>3</sub> and (b) BaTiO<sub>3</sub>-PTFE composite films fabricated by AD.



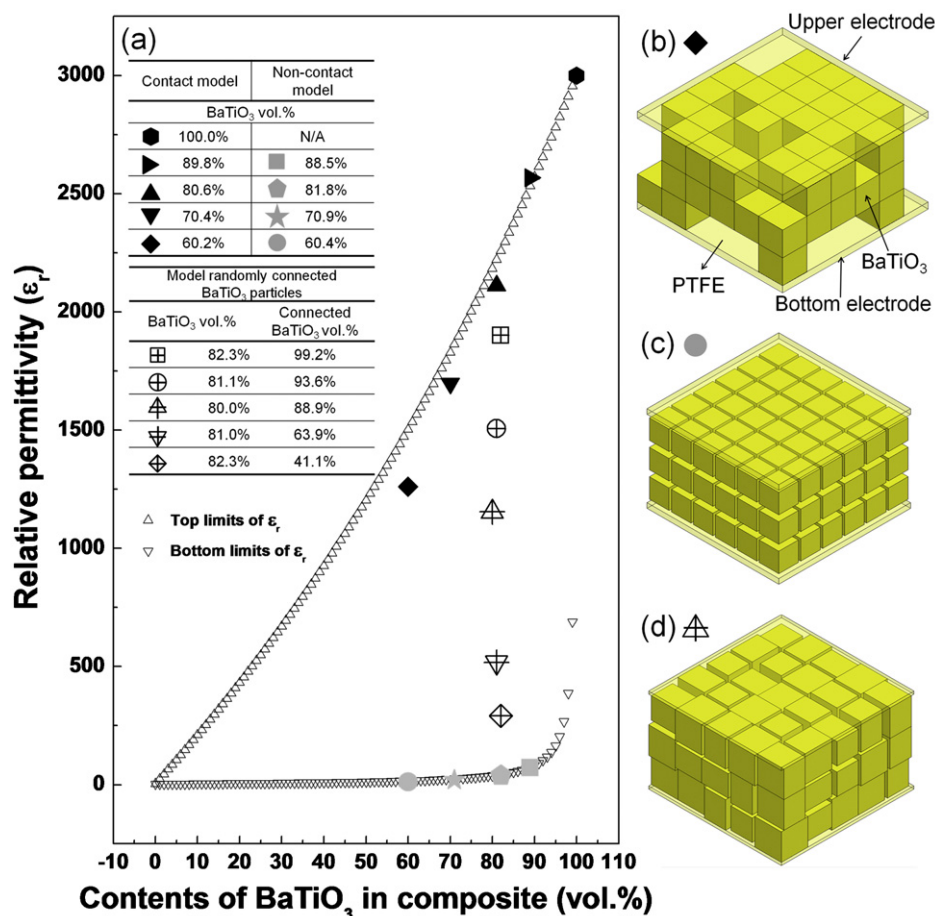


Fig. 6. (a) Hashin–Shtrikman bounds of BaTiO<sub>3</sub>-PTFE composites model as a function of BaTiO<sub>3</sub> content, (b) contact model with a BaTiO<sub>3</sub> content of 60.2 vol.%, (c) non-contact models with a BaTiO<sub>3</sub> content of 60.4 vol.%, and (d) model with 88.9 vol.% of the BaTiO<sub>3</sub> particles randomly connected.

that the connectivity between ceramic particles is a highly critical factor for achieving high permittivity. Achieving such connectivity between ceramic particles in the conventional polymer composite process is very difficult due to the resulting dispersion of the powder in the suspensions. In the AD process, the physical acceleration of the ceramic particles can be used to increase the connectivity between ceramic particles.

#### 4. Conclusions

This article has proposed the AD process as a suitable fabrication method for BaTiO<sub>3</sub>-PTFE composite films applied to embedded capacitors. The BaTiO<sub>3</sub> and BaTiO<sub>3</sub>-PTFE composite thick films were successfully fabricated by AD at room temperature. The decrement in the BaTiO<sub>3</sub> particle size was reduced and the distortion of the crystal structures was relieved in the BaTiO<sub>3</sub>-PTFE composite films due to the elasticity of the PTFE material. However, the relative permittivity of composite films was too low compared with that of the BaTiO<sub>3</sub> films. The prediction of the dielectric constant in the composite models using Hashin–Shtrikman bounds theory and 3-D electrostatic simulation confirmed the critical influence of the connectivity between the ceramic particles in attaining high permittivity in composite films.

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